



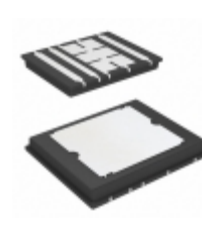
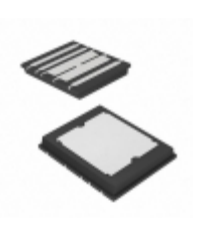
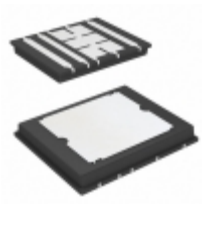
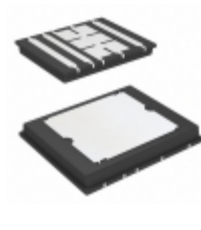
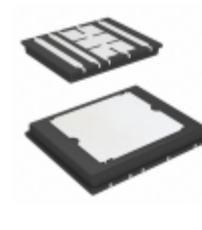
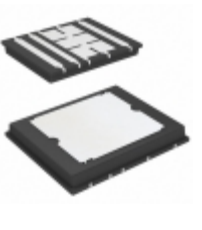
	<h2 style="color: #E67E22;">SIE808DF-T1-E3</h2>
	<p>Hersteller-Teilenummer: SIE808DF-T1-E3</p> <hr/> <p>Hersteller / Marke: Vishay / Siliconix</p> <hr/> <p>Teil der Beschreibung: MOSFET N-CH 20V 60A 10-POLARPAK</p> <hr/> <p>Datenblätter:  SIE808DF-T1-E3.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 1690 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIE808DF-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 60A 10-POLARPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1690 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	10-PolarPAK® (L)
Supplier Device-Gehäuse	10-PolarPAK® (L)
Verlustleistung (max)	5.2W (Ta), 125W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	60A (Tc)
Rds On (Max) @ Id, Vgs	1.6 mOhm @ 25A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	155nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	8800pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

SIE808DF-T1-E3 ist neu im Original, Suche SIE808DF-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIE808DF-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SIE808DF-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIE810DF-T1-E3 Vishay / Siliconix MOSFET N-CH 20V 60A 10-POLARPAK</p>	 <p>SIE808DF-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 60A 10-POLARPAK</p>	 <p>SIE810DF-T1-E3 Vishay / Spectrol MOSFET N-CH 20V 60A 10-POLARPAK</p>	 <p>SIE804DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 37A POLARPAK</p>
 <p>SIE806DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A POLARPAK</p>	 <p>SIE808DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 60A POLARPAK</p>	 <p>SIE808DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 60A POLARPAK</p>	 <p>SIE806DF-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A 10-POLARPAK</p>

heiße Teile

Mehr

⊕ 1812AC330KAT9A	↔ AIF64S355	⇒ B39881-B9432-M410-S05	D BCM5351GKPBG	⇒ BT136S-800G
⊖ CNH10R105M-TM	⊕ FDPF5N50NZU	D HCNW4502-300E	⇒ IPP10N03LBG	⇒ IXTP1R6N50D2
⊕ LD1117A-3.3	⊖ LT3480IMSE#TRPBF	⊕ LTC4251CS6#TR	↔ MB90098APF-G-149-BND-ER	⇒ MEA2010L201RT4S1
D MIC2954-03WS	⊕ MT28F200B5WG-8TET	⊖ PGD20012	⊕ PKA2431PIL	⇒ PTZTE256.2B
⇒ PV23P503C01B00	↔ RB520S-30LT1G	⊕ RT9163-50PG	⊖ SI2327DS-T1-GE3	⇒ SIE01-03
↔ SIE01-06	⇒ SIE20031	D SIE20034	⊕ SIE501.8LT	⊖ SIE503.3LT
⊕ SIE503.3LTR	D SIE800DF-T1-E3	⇒ SIE800DF-T1-E3	↔ SIE802DF-T1-E3	⇒ SIE802DF-T1-E3
⊖ SIE808DF-T1-E3	⊕ SIE812DF	↔ SIE848DF-T1-E3	⇒ SIE848DF-T1-E3	⇒ SIE862DF-T1-GE3
⊕ SIE862DF-T1-GE3	⊖ SIE864DP-T1-GE3	⊕ SIE874DF-T1-GE3	D SIE874DF-T1-GE3	⇒ SKB26E/14
↔ SPP1071S72RGB	⊕ T1203N08TOF	⊖ TDA1591T/N3	⊕ TPS79501DRBRG4	⇒ UCLAMP0501T.TCT

Contact us: Info@Y-IC.com

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